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November 2013

FDD7N20TM

N-Channel UniFETTM MOSFET 200 V, 5 A, 690 m Ω

Features

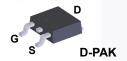
- $R_{DS(on)}$ = 580 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 2.5 A
- · Low Gate Charge (Typ. 5 nC)
- Low C_{rss} (Typ. 5 pF)
- · 100% Avalanche Tested
- · RoHS Compliant

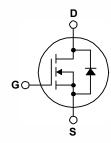
Applications

- LCD/LED/PDP TV
- · Consumer Appliances
- Lighting
- · Uninterruptible Power
- AC-DC Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol		Parameter			Unit	
V_{DSS}	Drain to Source Voltage			200	V	
V_{GSS}	Gate to Source Voltage			±30	V	
	- Continuous (T _C = 25°C)			5	^	
ID	Drain Current	- Continuous (T _C = 100°C)		3	A	
I _{DM}	Drain Current	Drain Current - Pulsed (Note 1)		15	Α	
E _{AS}	Single Pulsed Avalanche E	nergy	(Note 2)	62.5	mJ	
I _{AR}	Avalanche Current		(Note 1)	5	Α	
E _{AR}	Repetitive Avalanche Energy (Note 1)		(Note 1)	4.3	mJ	
dv/dt	Peak Diode Recovery dv/d	t	(Note 3)	4.5	V/ns	
Б	Dower Discinction	$(T_C = 25^{\circ}C)$		43	W	
P_{D}	Power Dissipation	- Derate Above 25°C		0.34	W/°C	
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +150	°C	
TL	Maximum Lead Temperatu	re for Soldering, 1/8" from Case for 5 Se	econds	300	°C	

Thermal Characteristics

Symbol	Parameter	FDD7N20TM	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max. 2.9		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.		30/00

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDD7N20TM	FDD7N20	DPAK	Tape and Reel	330 mm	16 mm	2500 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
Off Charac	cteristics					
BV _{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_J = 25^{\circ} C$	200	-	-	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I_D = 250 μ A, Referenced to 25°C	-	0.2	-	V/°C
1	Zero Gate Voltage Drain Current	V _{DS} = 200 V, V _{GS} =0 V	-	-	1	μΑ
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 160 \text{ V}, T_C = 125^{\circ}\text{C}$	-	-	10	μΑ
I _{GSS}	Gate to Body Leakage Current	V _{GS} = ±30 V, V _{DS} = 0 V	-	-	±100	nA

On Characteristics

V _{GS(th)}	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu\text{A}$	3.0	-	5.0	V
R _{DS(on)}	Static Drain to Source On Resistance	$V_{GS} = 10 \text{ V}, I_D = 2.5 \text{ A}$	-	0.58	0.69	Ω
9 _{FS}	Forward Transconductance	$V_{DS} = 40 \text{ V}, I_{D} = 2.5 \text{ A}$	-	6.2	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance	V 05 V V 0 V		-	185	250	pF
Coss	Output Capacitance	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz		-	45	65	pF
C _{rss}	Reverse Transfer Capacitance	1 - 1 1/11/12		-\	5	10	pF
Q_g	Total Gate Charge at 10V	V _{DO} = 160 V I _D = 7 A		- \	5	6.7	nC
Q _{gs}	Gate to Source Gate Charge	$V_{DS} = 160 \text{ V}, I_D = 7 \text{ A}, $ $V_{GS} = 10 \text{ V}$		- \	1.7	-	nC
Q_{gd}	Gate to Drain "Miller" Charge		(Note 4)	-	2.4	-	nC

Switching Characteristics

t _{d(on)}	Turn-On Delay Time		-	9	28	ns
t _r	Turn-On Rise Time	$V_{DD} = 100 \text{ V}, I_D = 7 \text{ A},$	-	30	70	ns
t _{d(off)}	Turn-Off Delay Time	V_{GS} = 10 V, R_G = 25 Ω	-	13	36	ns
t _f	Turn-Off Fall Time	(Note 4)	-	10	30	ns

Drain-Source Diode Characteristics

Is	Maximum Continuous Drain to Source Diode Forward Current		-	-	5	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	20	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 5 A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 7 A,	-	120	-	ns
Q _{rr}	Reverse Recovery Charge	dI _F /dt = 100 A/μs	-	0.4	_	μC

Notes:

- Repetitive rating: pulse-width limited by maximum junction temperature.
- 2. L =5 mH, I $_{AS}$ = 5 A, V $_{DD}$ = 50 V, R $_{G}$ = 25 $\Omega,$ starting T $_{J}$ = 25 $^{\circ}C.$
- 3. I $_{SD} \leq 5$ A, di/dt ≤ 200 A/µs, V $_{DD} \leq BV _{DSS},$ starting T $_{J}$ = 25°C.
- 4. Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

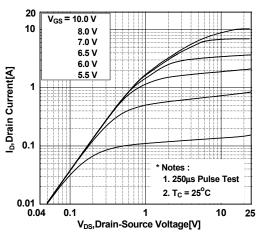


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

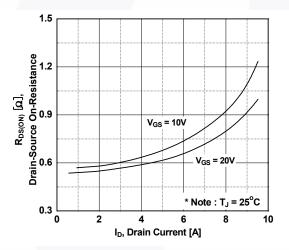


Figure 5. Capacitance Characteristics

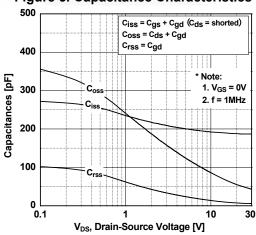


Figure 2. Transfer Characteristics

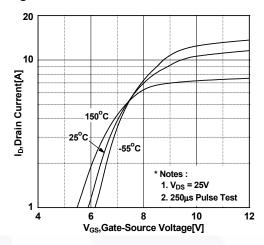


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

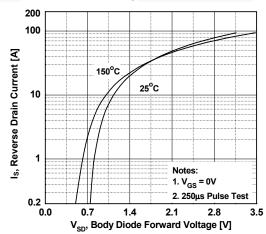
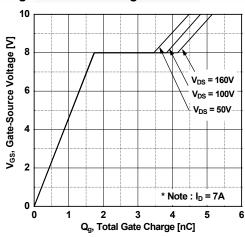


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

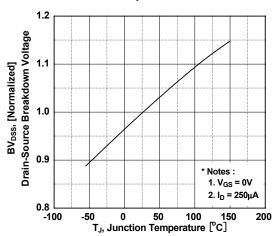


Figure 9. Maximum Safe Operating Area

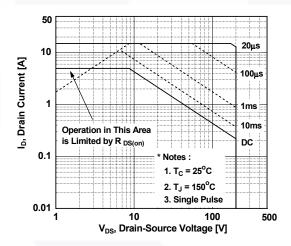


Figure 8. On-Resistance Variation vs. Temperature

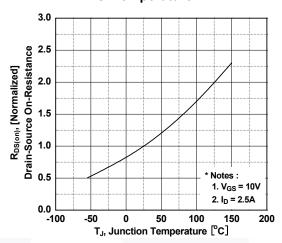


Figure 10. Maximum Drain Current vs. Case Temperature

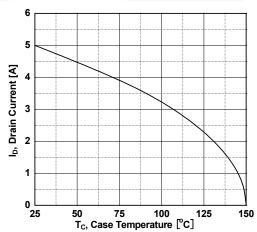
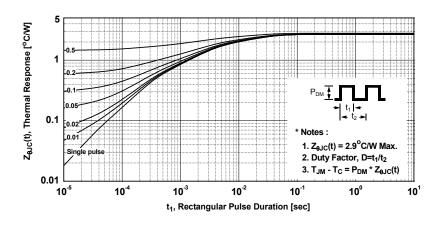


Figure 11. Transient Thermal Response Curve



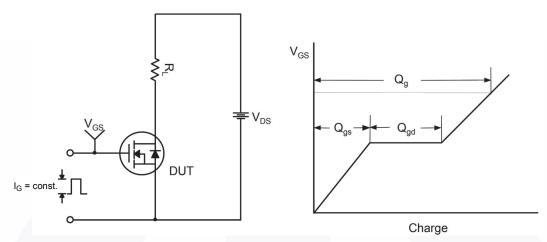


Figure 12. Gate Charge Test Circuit & Waveform



Figure 13. Resistive Switching Test Circuit & Waveforms



Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

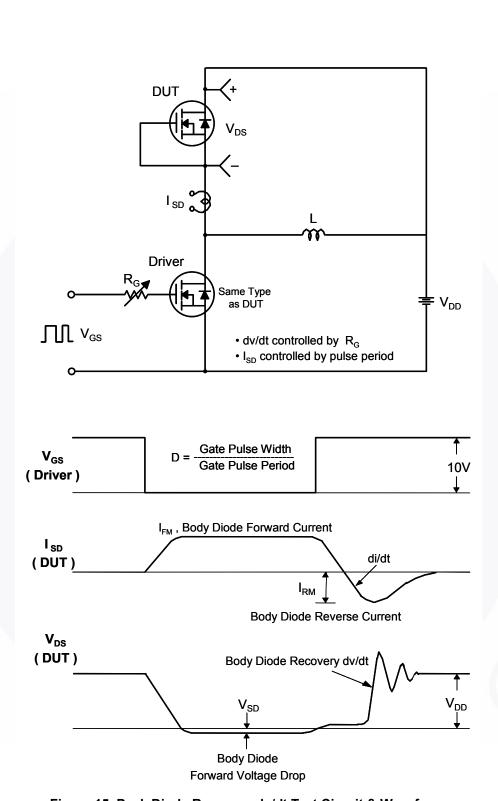


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

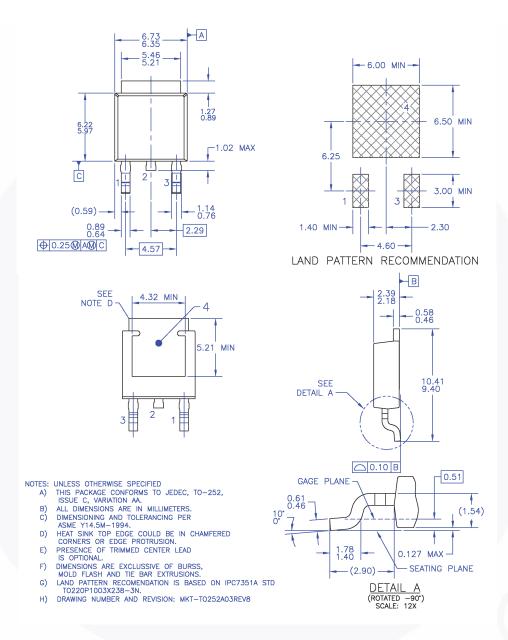


Figure 16. TO252 (D-PAK), Molded, 3-Lead, Option AA&AB

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